PROCESS CPD92

Schottky Diode

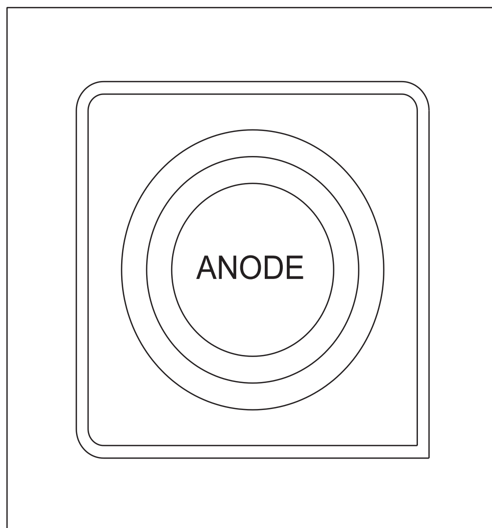
High Voltage Schottky Diode Chip

Central™ Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	9.0 x 9.0 MILS
Die Thickness	7.9 MILS
Anode Bonding Pad Area	4.8 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



R0

BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

139,050

PRINCIPAL DEVICE TYPES

CMDD6263
CMKD6263
CMOD6263
CMPD6263 SERIES
CMSD6263 SERIES
1N6263

145 Adams Avenue
Hauppauge, NY 11788 USA
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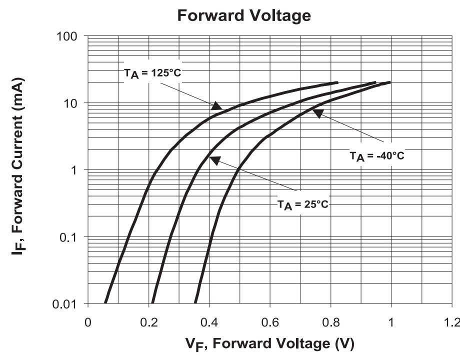
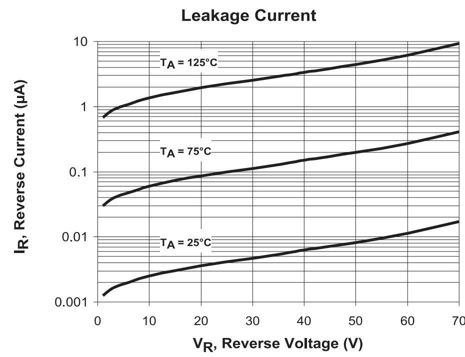
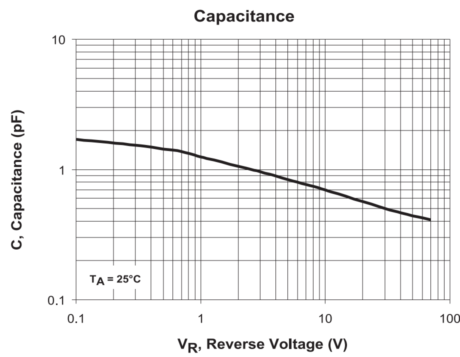
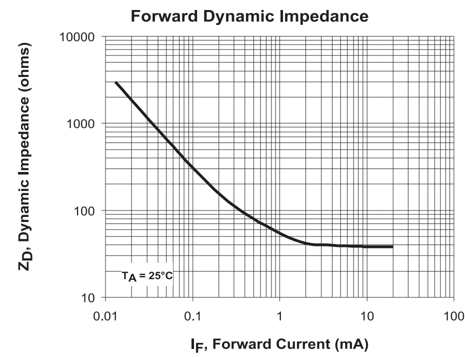
PROCESS CPD92

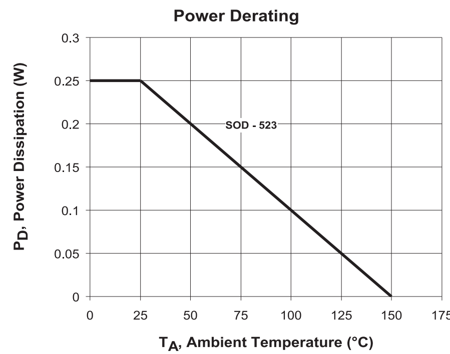
Typical Electrical Characteristics











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